

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of



Confirmation No. 8985

SOTOME, Yoshihiro

Allowed: February 18, 2004

Serial No. 10/038,680

Atty. Ref.: 900-410

Filed: January 8, 2002

Group: 2825

Examiner: Lee, Calvin

For: METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE AND THE  
SEMICONDUCTOR DEVICE MANUFACTURED BY THE METHOD

\* \* \* \* \*

May 7, 2004

**Mail Stop: Issue Fee**  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE**

The instant application was allowed February 18, 2004. However, the Reasons for Allowance are not commensurate with the scope of the claims.

For example, and without limitation, claim 13 does not require thermal treating for forming a second silicide film "on a substrate's surface" as recited in the reasons for allowance.

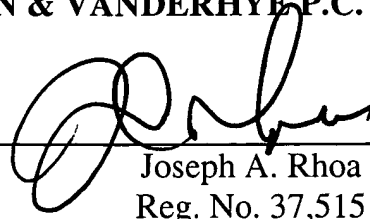
Please let me know if you should have any questions.

**SOTOME, Yoshihiro**  
Serial No. **10/038,680**

Respectfully submitted,

**NIXON & VANDERHYE P.C.**

By: \_\_\_\_\_

A handwritten signature in black ink, appearing to read "Joseph A. Rhoa", written over a horizontal line.

Joseph A. Rhoa  
Reg. No. 37,515

JAR:caj  
1100 North Glebe Road, 8th Floor  
Arlington, VA 22201-4714  
Telephone: (703) 816-4000  
Facsimile: (703) 816-4100